

Radiation Hardened EDAC (Error Detection and Correction Circuit)

January 1996

Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96711 and Intersil' QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Total Dose >300K RAD (Si)
- Single Event Upset (SEU) Immunity: <1 x 10⁻¹⁰ Errors/Bit/Day (Typ)
- SEU LET Threshold >100 MEV-cm²/mg
- Dose Rate Upset >10¹¹ RAD (Si)/s, 20ns Pulse
- Dose Rate Survivability >10¹² RAD (Si)/s, 20ns Pulse
- Latch-Up Free Under Any Conditions
- Military Temperature Range -55°C to +125°C
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range 4.5V to 5.5V
- Input Logic Levels
 - VIL = 30% of VCC Max
 - VIH = 70% of VCC Min
- Input Current ≤ 1μA at VOL, VOH
- Fast Propagation Delay 37ns (Max), 24ns (Typ)

Description

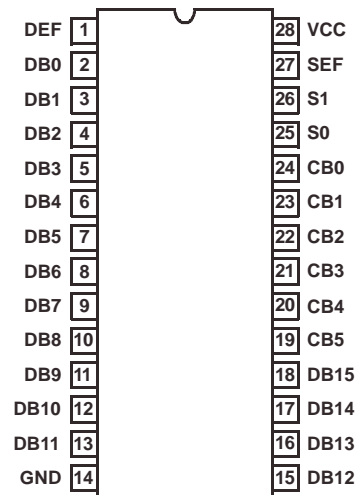
The Intersil ACS630MS is a Radiation Hardened 16-bit parallel error detection and correction circuit. It uses a modified Hamming code to generate a 6-bit check word from each 16-bit data word. The check word is stored with the data word during a memory write cycle; during a memory read cycle a 22-bit word is taken from memory and checked for errors. Single bit errors in the data words are flagged and corrected. Single bit errors in check words are flagged but not corrected. The position of the incorrect bit is pinpointed, in both cases, by the 6-bit error syndrome code which is output during the error correction cycle.

The ACS630MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of a radiation hardened, high-speed, CMOS/SOS Logic Family.

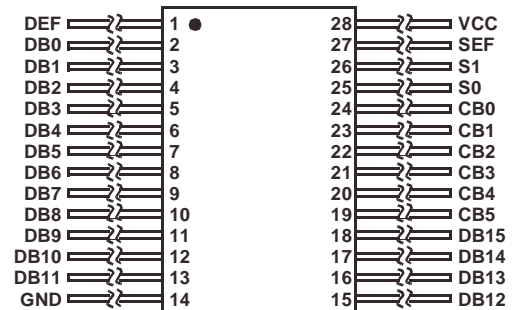
The ACS630MS is supplied in a 28 lead Ceramic Flatpack (K suffix) or a 28 Lead Ceramic Dual-In-Line Package (D suffix).

Pinouts

28 PIN CERAMIC DUAL-IN-LINE, MIL-STD-1835
DESIGNATOR CDIP2-T28, LEAD FINISH C
TOP VIEW



28 PIN CERAMIC FLATPACK, MIL-STD-1835
DESIGNATOR CDFP3-F28, LEAD FINISH C
TOP VIEW



Ordering Information

| PART NUMBER | TEMPERATURE RANGE | SCREENING LEVEL | PACKAGE |
|-----------------|-------------------|-----------------------|--------------------------|
| 5962F9671101VXC | -55°C to +125°C | MIL-PRF-38535 Class V | 28 Lead SBDIP |
| 5962F9671101VYC | -55°C to +125°C | MIL-PRF-38535 Class V | 28 Lead Ceramic Flatpack |
| ACS630D/Sample | 25°C | Sample | 28 Lead SBDIP |
| ACS630K/Sample | 25°C | Sample | 28 Lead Ceramic Flatpack |
| ACS630HMSR | 25°C | Die | Die |

ACS630MS

Function Tables

Control Functions

| MEMORY CYCLE | CONTROL | | EDAC FUNCTION | DATA I/O | CHECKWORD | ERROR FLAGS | |
|--------------|---------|------|--|-----------------------|----------------------|-------------|---------|
| | S1 | S0 | | | | SEF | DEF |
| WRITE | Low | Low | Generates Checkword | Input Data | Output Checkword | Low | Low |
| READ | Low | High | Read Data and Checkword | Input Data | Input Checkword | Low | Low |
| READ | High | High | Latch and Flag Error | Latch Data | Latch Checkword | Enabled | Enabled |
| READ | High | Low | Correct Data Word and Generate Syndrome Bits | Output Corrected Data | Output Syndrome Bits | Enabled | Enabled |

Check Word Generation

| CHECKWORD BIT | 16-BIT DATA WORD | | | | | | | | | | | | | | | |
|---------------|------------------|---|---|---|---|---|---|---|---|---|----|----|----|----|----|----|
| | 0 | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 | 15 |
| CB0 | X | X | | X | X | | | | X | X | X | | | X | | |
| CB1 | X | | X | X | | X | X | | X | | | X | | | X | |
| CB2 | | X | X | | X | X | | X | | X | | | X | | | X |
| CB3 | X | X | X | | | | X | X | | | X | X | X | | | |
| CB4 | | | | X | X | X | X | X | | | | | | X | X | X |
| CB5 | | | | | | | | | X | X | X | X | X | X | X | X |

NOTE: The six check bits are parity bits derived from the matrix of data bits as indicated by "x" for each bit

Error Syndrome Codes

| SYNDROME ERROR CODE | ERROR LOCATIONS | | | | | | | | | | | | | | | | | | | | | | | |
|---------------------|-----------------|---|---|---|---|---|---|---|---|---|----|----|----|----|----|----|---|---|---|---|---|----------|---|---|
| | DB | | | | | | | | | | | | | | | CB | | | | | | NO ERROR | | |
| | 0 | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 | 15 | 0 | 1 | 2 | 3 | 4 | | 5 | |
| CB0 | L | L | H | L | L | H | H | H | L | L | L | H | H | L | H | H | L | H | H | H | H | H | H | H |
| CB1 | L | H | L | L | H | L | L | H | L | H | H | L | H | H | L | H | H | L | H | H | H | H | H | H |
| CB2 | H | L | L | H | L | L | H | L | H | L | H | H | L | H | H | L | H | H | L | H | H | H | H | H |
| CB3 | L | L | L | H | H | H | L | L | H | H | L | L | L | H | H | H | H | H | H | L | H | H | H | H |
| CB4 | H | H | H | L | L | L | L | L | H | H | H | H | H | L | L | L | H | H | H | H | L | H | H | H |
| CB5 | H | H | H | H | H | H | H | H | L | L | L | L | L | L | L | L | H | H | H | H | H | L | H | H |

Error Functions

| TOTAL NUMBER OF ERRORS | | ERROR FLAGS | | DATA CORRECTION |
|------------------------|-----------------|-------------|------|-----------------|
| 16-BIT DATA | 6-BIT CHECKWORD | SEF | DEF | |
| 0 | 0 | Low | Low | Not Applicable |
| 1 | 0 | High | Low | Correction |
| 0 | 1 | High | Low | Correction |
| 1 | 1 | High | High | Interrupt |
| 2 | 0 | High | High | Interrupt |
| 0 | 2 | High | High | Interrupt |

ACS630MS

Die Characteristics

DIE DIMENSIONS:

171 mils x 159 mils
4340mm x 4040mm

METALLIZATION:

Type: AlSi
Metal 1 Thickness: $7.125\text{k}\text{\AA} \pm 1.125\text{k}\text{\AA}$
Metal 2 Thickness: $9\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

GLASSIVATION:

Type: SiO_2
Thickness: $8\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

WORST CASE CURRENT DENSITY:

$<2.0 \times 10^9 \text{A/cm}^2$

BOND PAD SIZE:

$110\mu\text{m} \times 110\mu\text{m}$
4.4 mils x 4.4 mils

Metallization Mask Layout

